



## BUL7216

### HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

#### Features

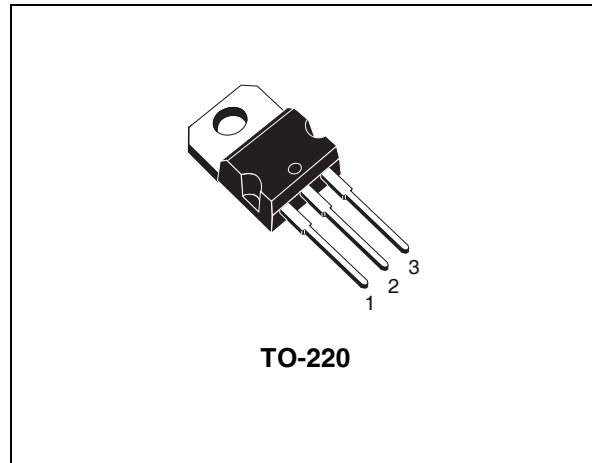
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED

#### Applications

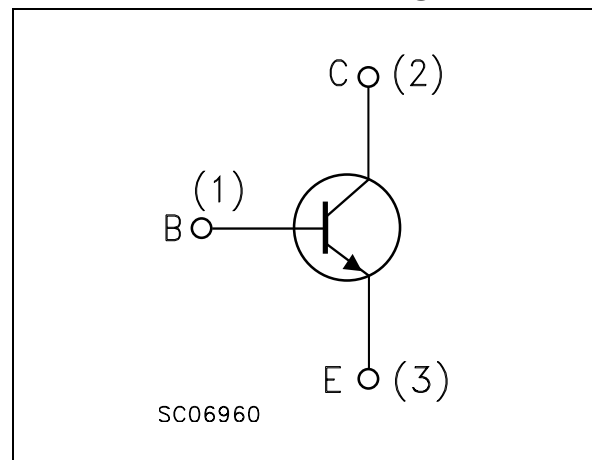
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING (277V PUSH-PULL AND 347V HALF BRIDGE TOPOLOGIES)

#### Description

The BUL7216 is a new device manufactured using Diffused Collector technology to enhance switching speeds and tight  $h_{FE}$  while maintaining the wide RBSOA.



#### Internal Schematic Diagram



#### Order Codes

Part Number	Marking	Package	Packing
BUL7216	BUL7216	TO-220	TUBE

# 1 Absolute Maximum Ratings

**Table 1. Absolute Maximum Rating**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	1600	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	700	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	12	V
$I_C$	Collector Current	3	A
$I_{CM}$	Collector Peak Current ( $t_P < 5\text{ms}$ )	6	A
$I_B$	Base Current	1	A
$I_{BM}$	Base Peak Current ( $t_P < 5\text{ms}$ )	1.5	A
$P_{tot}$	Total dissipation at $T_C = 25^\circ\text{C}$	80	W
$T_{stg}$	Storage Temperature	-65 to 150	$^\circ\text{C}$
$T_J$	Max. Operating Junction Temperature	150	$^\circ\text{C}$

**Table 2. Thermal Data**

Symbol	Parameter	Value	Unit
$R_{thJ-case}$	Thermal Resistance Junction-Case Max	1.56	$^\circ\text{C/W}$

## 2 Electrical Characteristics

**Table 3. Electrical Characteristics** ( $T_{CASE} = 25^{\circ}C$ ; unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CES}$	Collector Cut-off Current ( $V_{BE} = 0$ )	$V_{CE} = 1600\text{ V}$			0.1	mA
		$V_{CE} = 1600\text{ V}$ $T_C = 125^{\circ}C$			0.5	mA
$I_{CEO}$	Collector Cut-off Current ( $I_B = 0$ )	$V_{CE} = 680\text{ V}$			0.1	mA
$I_{CBO}$	Collector Cut-off Current ( $I_E = 0$ )	$V_{CB} = 1600\text{ V}$			0.1	mA
		$V_{CB} = 1600\text{ V}$ $T_C = 125^{\circ}C$			0.5	mA
$I_{EBO}$	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = 12\text{ V}$			1	mA
$V_{(BR)CEO}$ <i>Note: 1</i>	Collector-Emitter Breakdown Voltage ( $I_B = 0$ )	$I_C = 1\text{ mA}$ $L = 125\text{ mH}$	700			V
$V_{(BR)EBO}$ <i>Note: 1</i>	Emitter-Base Breakdown Voltage ( $I_C = 0$ )	$I_E = 1\text{ mA}$	12			V
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ( $V_{BE} = 0$ )	$I_C = 0.1\text{ mA}$	1600			V
$V_{CE(sat)}$ <i>Note: 1</i>	Collector-Emitter Saturation Voltage	$I_C = 0.25\text{ A}$ $I_B = 25\text{ mA}$			1	V
		$I_C = 0.5\text{ A}$ $I_B = 50\text{ mA}$			1.5	V
		$I_C = 0.8\text{ A}$ $I_B = 80\text{ mA}$			3	V
$V_{BE(sat)}$ <i>Note: 1</i>	Base-Emitter Saturation Voltage	$I_C = 0.5\text{ A}$ $I_B = 100\text{ mA}$			1	V
		$I_C = 1\text{ A}$ $I_B = 100\text{ mA}$			1.1	V
		$I_C = 2\text{ A}$ $I_B = 400\text{ mA}$			1.2	V
$h_{FE}$ <i>Note: 1</i>	DC Current Gain	$I_C = 0.5\text{ A}$ $V_{CE} = 1\text{ V}$	7		18	
		$I_C = 0.5\text{ A}$ $V_{CE} = 3\text{ V}$	16		35	
		$I_C = 2\text{ A}$ $V_{CE} = 5\text{ V}$	4		11	
		$I_C = 1\text{ A}$ $V_{CE} = 10\text{ V}$	19			
$t_s$ $t_f$	RESISTIVE LOAD Storage Time	$I_C = 0.5\text{ A}$ $V_{CC} = 125\text{ V}$ $I_{B1} = 50\text{ mA}$ $I_{B2} = -0.5\text{ A}$ P.W. = 300 $\mu\text{s}$ D.C. = 2 % (see figure 9)			0.9	$\mu\text{s}$
	Fall Time				0.35	$\mu\text{s}$
$t_d$ $t_r$	RESISTIVE LOAD Delay Time	$I_C = 0.5\text{ A}$ $V_{CC} = 125\text{ V}$ $I_{B1} = 50\text{ mA}$ $I_{B2} = -0.5\text{ A}$ P.W. = 300 $\mu\text{s}$ D.C. = 2 % (see figure 9)			0.3	$\mu\text{s}$
	Rise Time				1.1	$\mu\text{s}$
$E_{a/r}$	Repetitive Avalanche Energy	$L = 2\text{ mH}$ $C = 1.8\text{ nF}$ $V_{BE(off)} = -5\text{ V}$ (see figure 8)	8			mJ

*Note: 1 Pulsed duration = 300  $\mu\text{s}$ , duty cycle  $\leq 1.5\%$ .*

## 2.1 Typical Characteristics

Figure 1. DC Current Gain

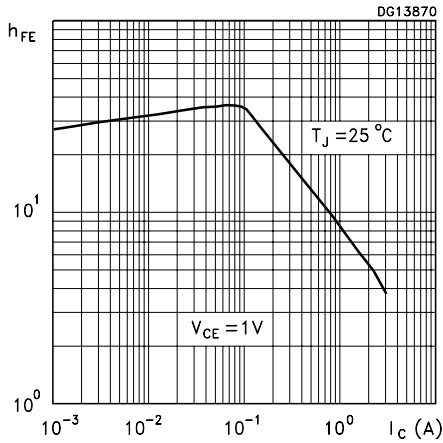


Figure 2. DC Current Gain

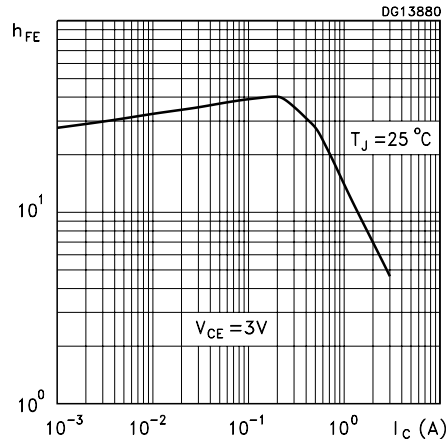


Figure 3. Collector- Emitter Saturation Voltage

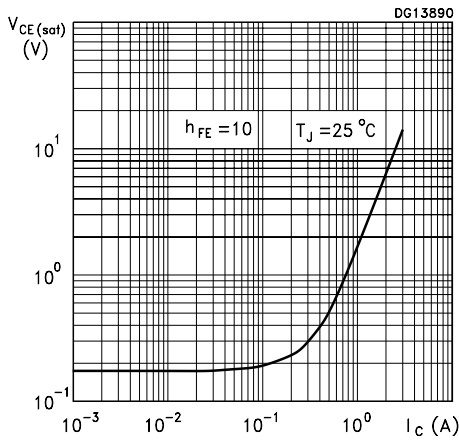


Figure 4. Base-Emitter Saturation Voltage

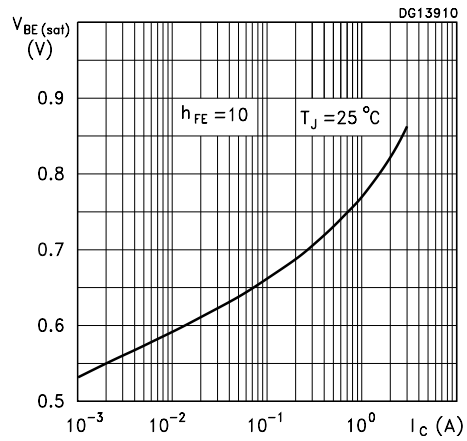


Figure 5. Resistive Load Switching Time

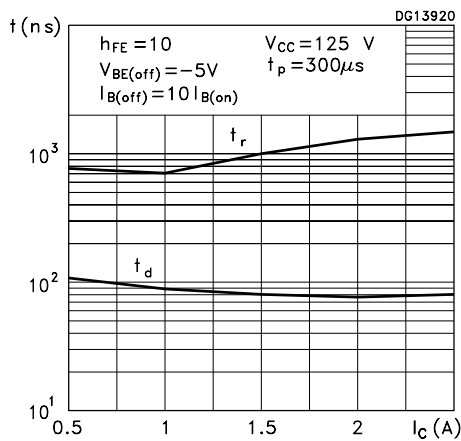


Figure 6. Resistive Load Switching Time

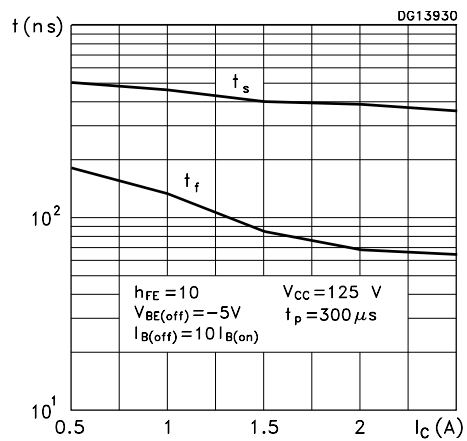
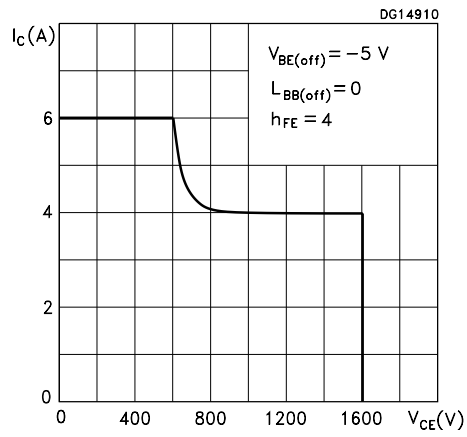


Figure 7. Reverse Biased Safe Operating Area



### 3 Test Circuits

Figure 8. Energy Rating Test Circuit

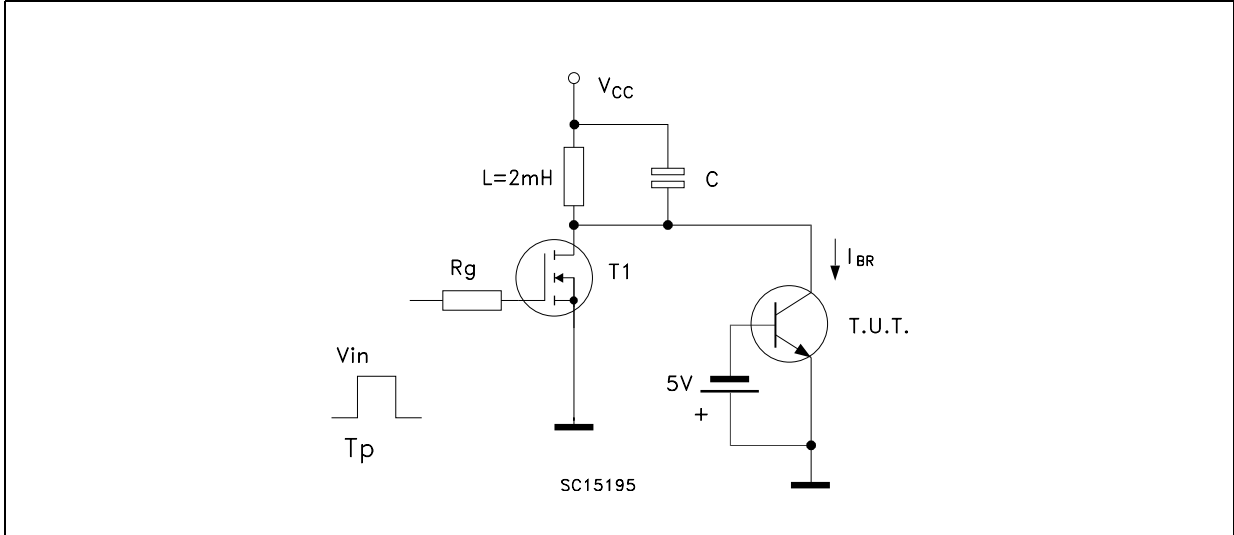
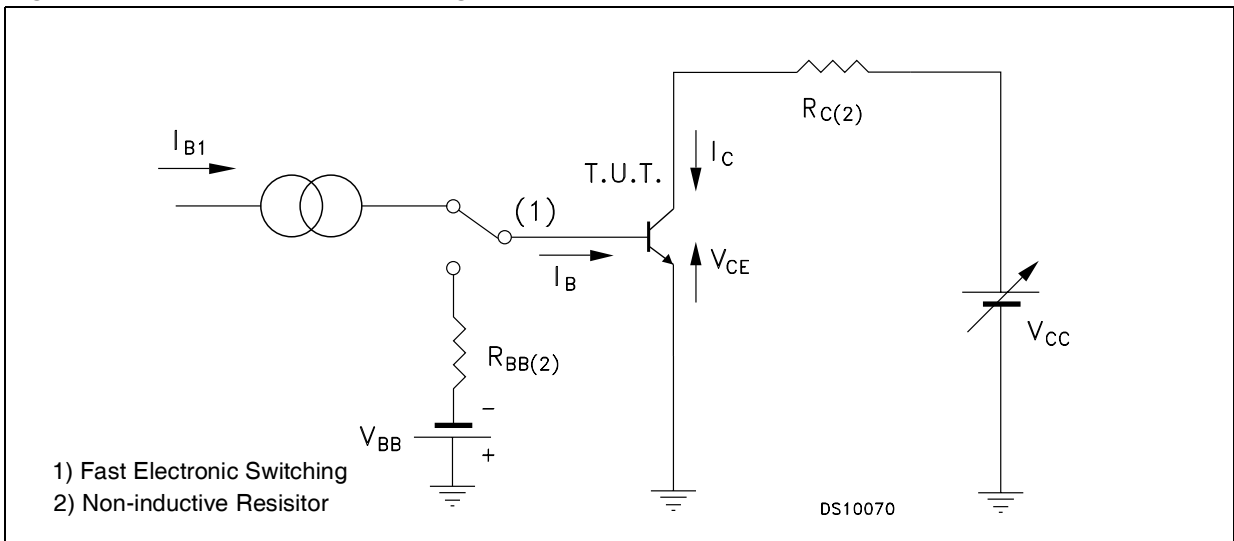


Figure 9. Resistive Load Switching Test Circuits

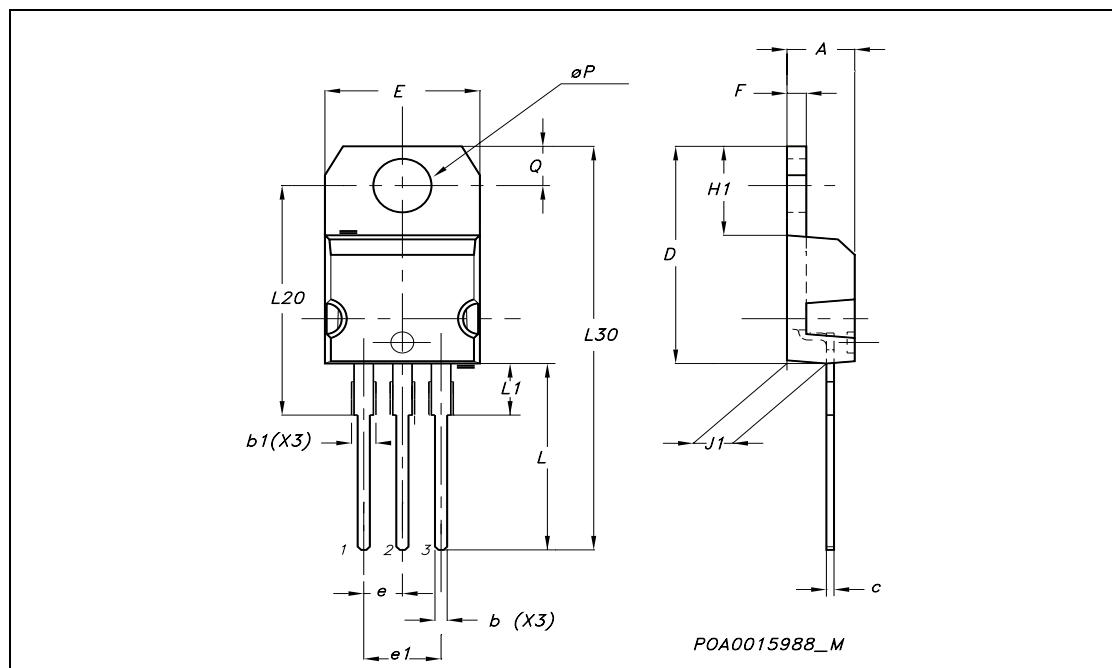


## 4 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

**TO-220 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116





## 5 Revision History

Date	Revision	Changes
17-Jan-2006	1	Initial Release

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.  
All other names are the property of their respective owners

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -  
Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

[www.st.com](http://www.st.com)